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(54) **CAPACITOR, SEMICONDUCTOR DEVICE
INCLUDING THE SAME AND ELECTRONIC
APPARATUS**

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ABSTRACT

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Provided is a capacitor, a semiconductor device including the same, and an electronic apparatus including the semiconductor device, wherein the capacitor includes a first electrode including a first metal ion, a second electrode arranged spaced apart from the first electrode, a dielectric layer provided between the first electrode and the second electrode, and an interfacial layer provided between the first electrode and the dielectric layer and including a compound represented by $M_xO_yN_z$, in which a diffusion energy barrier value of M is equal to or greater than a diffusion energy barrier value of the first metal ion.

